

DOCKET NO. SC11805TP

Please amend the subject application as follows:

IN THE SPECIFICATION:

On page 1, lines 1 and 2, amend the title as follows:

**METHOD OF FORMING A VERTICAL DOUBLE GATE SEMICONDUCTOR DEVICE
AND STRUCTURE THEREOF**

On page 22, lines 1 and 2, amend the title as follows:

**METHOD OF FORMING A VERTICAL DOUBLE GATE SEMICONDUCTOR DEVICE
AND STRUCTURE THEREOF**